



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of : **Confirmation No. 4860**
Hirotooshi KUBO : **Docket No. 2001-1101**
Serial No. 09/919,797 : **Group Art Unit 2822**
Filed August 2, 2001 : **Examiner Jeff B Vockrodt**

HIGH FREQUENCY TRANSISTOR DEVICE :

SUPPLEMENTAL AMENDMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

THE COMMISSIONER IS AUTHORIZED
TO CHARGE ANY DEFICIENCY IN THE
FEE FOR THIS PAPER TO DEPOSIT
ACCOUNT NO. 23-0975.

Sir:

Please further amend the above-identified application as follows.

In the Claims:

Kindly amend claim 1 as follows.

1. (Twice Amended) A method of manufacturing a semiconductor device, comprising:
forming a collector layer of a first conductivity type;
forming a base region of a second conductivity type formed on a top surface of said collector layer of said first conductivity type, said first conductivity type being opposite said second conductivity type, said base region being formed using epitaxial growth technology, and being formed as a single region having a uniform depth;
forming a groove in a top surface of said base region at a portion thereof;
forming spacers on sidewalls of said groove;

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